



Micro Commercial Components
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2SC898

**NPN Silicon
Power Transistors**

Features

- With TO-3 package
- Amplifier applications

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	150	V
V_{CBO}	Collector-Base Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	7.0	A
P_C	Collector power dissipation	80	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

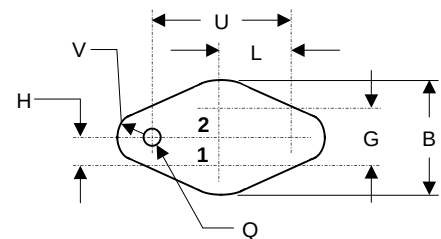
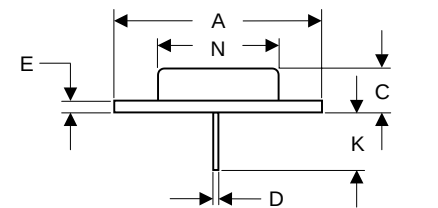
Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=50\text{mA}$, $I_B=0$)	150	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=150\text{Vdc}$, $I_E=0$)	---	1.0	mA
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=5.0\text{Vdc}$, $I_C=0$)	---	1.0	mA

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=1.0\text{A}$, $V_{CE}=5.0\text{Vdc}$)	50	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=6.0\text{A}$, $I_B=1.0\text{A}$)	---	1.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=6.0\text{A}$, $I_B=1.0\text{A}$)	---	1.8	Vdc

TO-3



PIN 1. BASE
PIN 2. EMITTER
CASE. COLLECTOR

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	1.550	REF	39.37	REF	
B	---	1.050	---	26.67	
C	.250	.335	6.35	8.51	
D	.038	.043	0.97	1.09	
E	0.55	0.70	1.40	1.77	
G	.430	BSC	10.92	BSC	
H	.215	BSC	5.46	BSC	
K	.440	.480	11.18	12.19	
L	.665	BSC	16.89	BSC	
N	---	.830	---	21.08	
Q	.151	.165	3.84	4.19	Ø
U	1.187	BSC	30.15	BSC	
V	.131	.188	3.33	4.77	